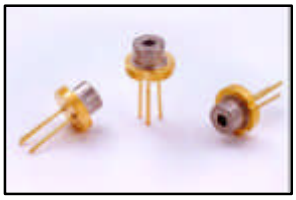
ROITHNER LASERTECHNIK

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TEL: +43 -1- 586 52 43 FAX: +43 -1- 586 41 43
e-mail: office@roithner-laser.com http://www.roithner-laser.com

RLT8810MG TECHNICAL DATA



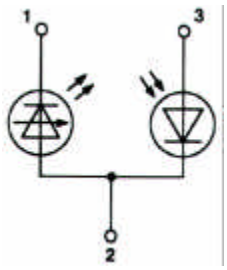
High Power Infrared Laserdiode

Structure: **index guided single transverse mode**
Lasing wavelength: **875 nm typ.**
Output power: **10 mW cw**
Package: **5.6 mm, TO-18**

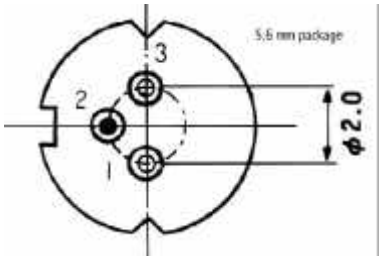


NOTE!
LASERDIODE
MUST BE COOLED!

PIN CONNECTION:



1) Laser diode cathode
2) Laser diode anode and photodiode cathode
3) Photodiode anode



Maximum Ratings (Tc = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P_o	10	mW
LD Reverse Voltage	$V_{R(LD)}$	2	V
PD Reverse Voltage	$V_{R(PD)}$	30	V
Operation Case Temperature	T_C	-10 .. +60	°C
Storage Temperature	T_{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Threshold Current	I_{th}	cw	7	10	15	mA
Operation Current	I_{op}	P_o = 10 mW	20	25	30	mA
Operating Voltage	V_{op}	P_o = 10 mW		1.65	1.8	V
Lasing Wavelength	λ_p	P_o = 10 mW		875	883	nm
Beam Divergence	$\theta_{//}$	P_o = 10 mW	9	10	12	°
Beam Divergence	$\theta_{\perp}$	P_o = 10 mW	30	33	38	°
Slope Efficiency	η	cw	0.5	0.7	1	mW/mA
Monitor Current	I_m	P_o = 10 mW		400	500	µA